PROCESS CPD41

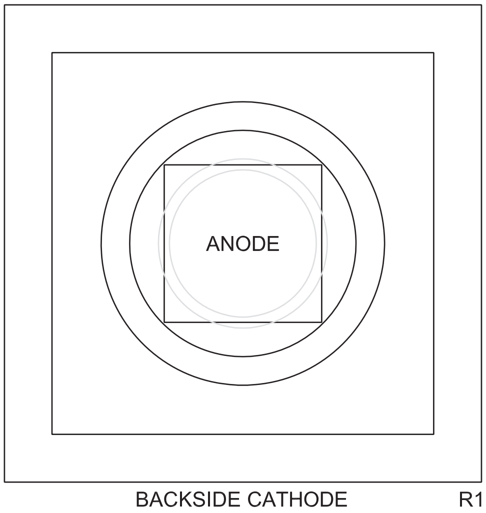
Switching Diode

High Current Switching Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	19.7 x 19.7 MILS
Die Thickness	8.0 MILS
Anode Bonding Pad Area	6.5 x 6.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER
30,394

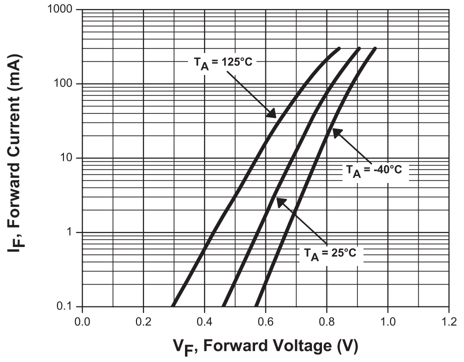
PRINCIPAL DEVICE TYPES
1N3600
1N4150
CMPD4150

R4 (22-March 2010)

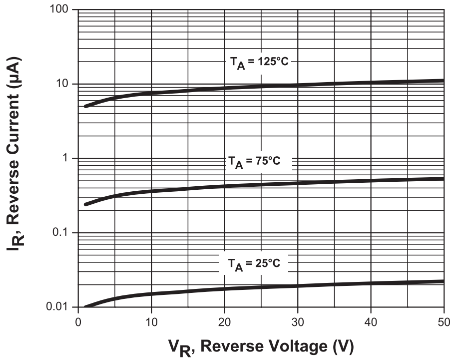
PROCESS CPD41

Typical Electrical Characteristics

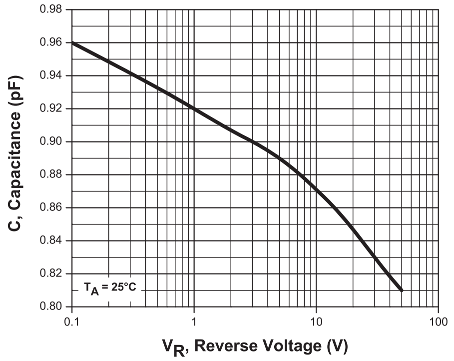
Forward Voltage



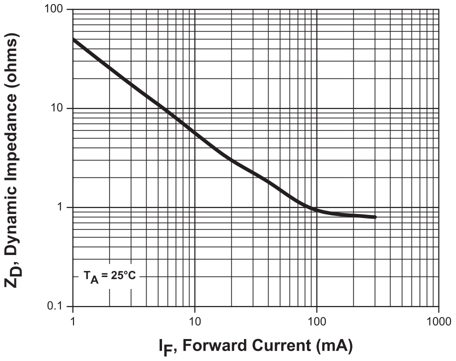
Leakage Current



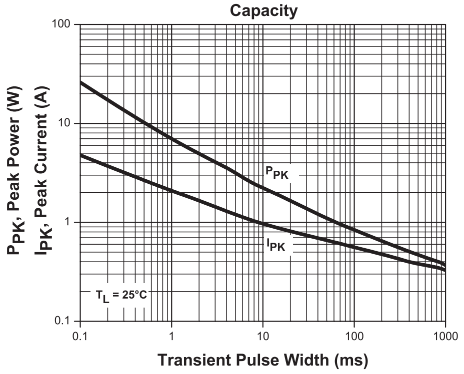
Capacitance



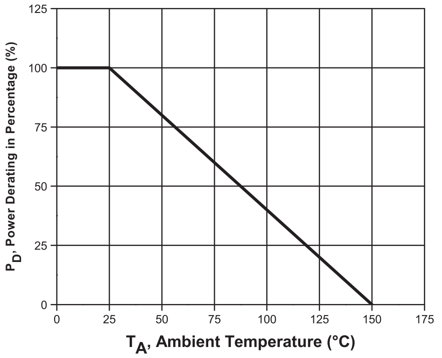
Forward Dynamic Impedance



Transient Peak Power and Peak Current Capacity



Normalized Power Derating



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